

# Generate Auxiliary Voltages at Low Cost

By John Betten, Application Engineer, Texas Instruments, Dallas

When a switching regulator generates the main output voltage, additional regulated outputs may be added using various configurations of coupled inductor or charge-pump circuits.

Frequently, the *lowest possible cost* is the fundamental challenge that engineers encounter when designing power converters. When multiple output voltages are required, it is often tempting to provide one switching regulator for each output voltage. While this approach provides excellent output-voltage regulation, it certainly does nothing to help achieve the top design priority — lowest possible cost.

Fortunately, circuits such as coupled inductors and charge pumps can be easily implemented in traditional switching converters to provide additional output-voltage rails at minimal cost. Using the proper circuit configuration, it is often possible to achieve good voltage regulation along with high efficiency.

## Coupled Inductors

Fig. 1 shows three different ways to generate an auxiliary output from a coupled inductor. In all three configurations, current flows in the auxiliary winding only during the on time of the synchronous FET. During this period of the

switching cycle, the  $V_{OUT1}$  output voltage plus the drain-to-source voltage ( $V_{GS}$ ) drop of the synchronous FET are impressed across the inductor's primary winding. The FET's voltage drop generally is quite small, usually less than 0.1 V, compared to around 0.5 V if a diode rectifier is used.

The auxiliary output voltage for an inductor with a 1:1 winding ratio is equal to the primary-winding voltage, less the forward-voltage drop of the secondary-side diode, or  $V_{OUT2} = V_{OUT1} + V_{FET} - V_D$ . The actual  $V_{OUT2}$  output voltage obtained is dependent on the load currents in both outputs since the voltage drops of  $V_{FET}$  and  $V_D$  are current dependent. Additionally, good coupling between the windings is necessary to reduce leakage-inductance effects at higher operating frequencies. Lower switching frequencies and light loading provide the best voltage regulation for  $V_{OUT2}$ .

As shown in Fig. 1, the ground reference of the auxiliary winding can be connected to any point. In circuit A, the  $V_{OUT2}$  ground can be connected to a separate, isolated ground (as shown) or to the  $V_{OUT1}$  ground if isolation is not required. In circuit B, the  $V_{OUT2}$  ground floats on top

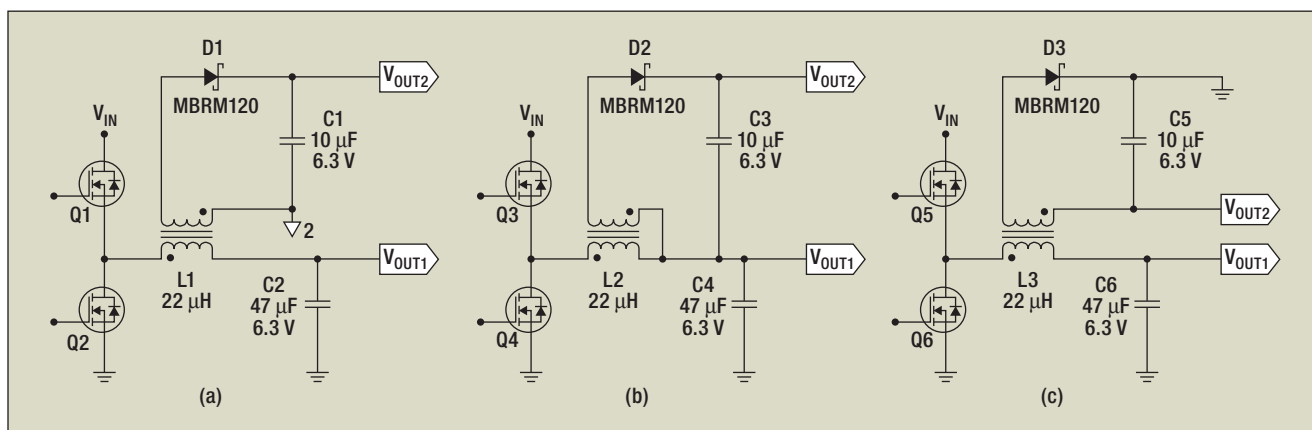
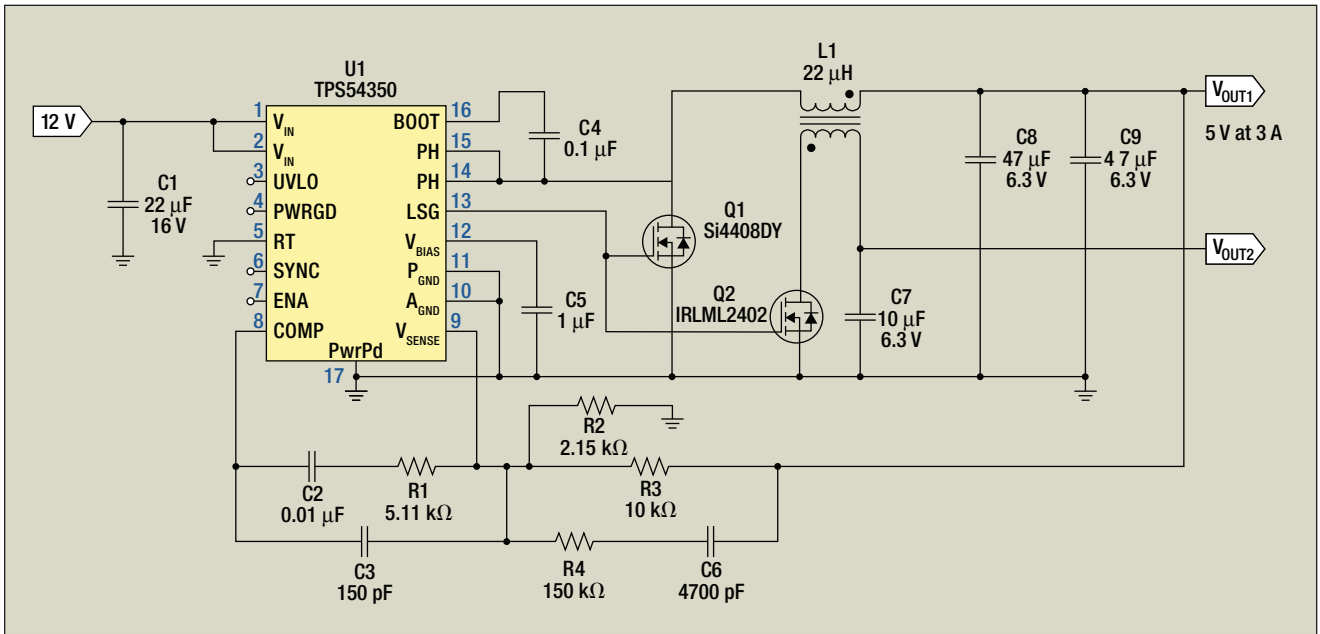
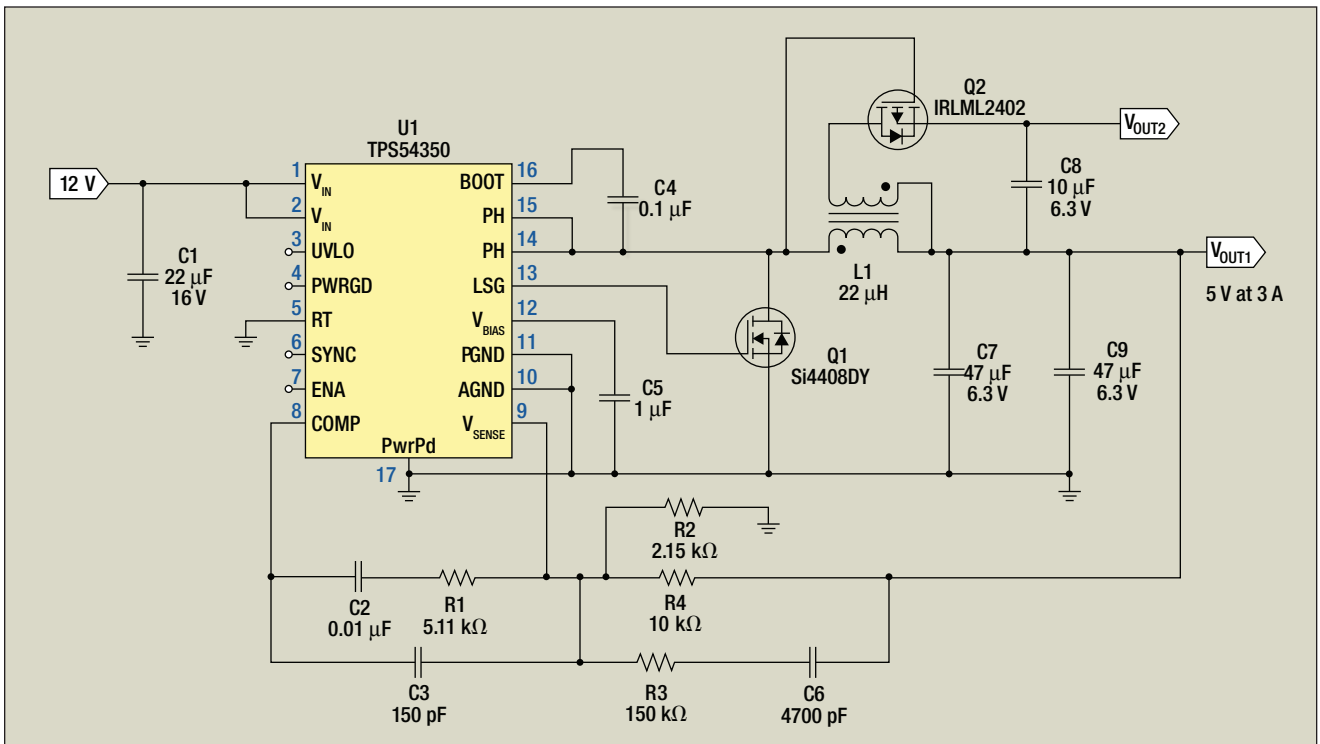


Fig. 1. Coupled inductors create design flexibility, allowing the auxiliary voltage ( $V_{OUT2}$ ) to be generated with an isolated (a) or nonisolated (b) ground, or as a negative voltage (c).





**Fig. 4.** Synchronous operation using all *n*-channel FETs improves the efficiency of  $V_{OUT2}$ .



**Fig. 5.** Synchronous operation of a coupled inductor using a *p*-channel FET eliminates the requirement for low-side gate drive for the FET associated with the auxiliary output ( $V_{OUT2}$ ).

drop of the diode can introduce a large output-voltage variation over load current and temperature. **Fig. 4** shows a circuit that uses secondary-side synchronous rectification to reduce the voltage variation and FET losses.

When low-resistance FETs are used, FET voltage drops are minimal and the output-voltage regulation for  $V_{OUT2}$  improves. Under certain loading conditions, the voltage drops of FETs Q1 and Q2 will perfectly cancel each other,

resulting in an output voltage for  $V_{OUT2}$  that is equal to  $V_{OUT1}$  times the turns ratio of the coupled inductor.

Excellent cross regulation and high efficiency can be achieved with this technique. The drawback is that access to the low-side FET gate-drive signal is required to drive the synchronous coupled-inductor FET. This eliminates the use of synchronous buck controllers that have integrated top and bottom FETs. The circuit in **Fig. 5** bypasses this

limitation by using a p-channel FET.

The Fig. 5 circuit operates identically to that of Fig. 4, except the gate drive to the p-channel FET is driven out-of-phase by the switch node, rather than the bottom FET gate drive. Care must be taken when a p-channel FET is used in this configuration that the gate-source voltage available is adequate to ensure full enhancement in steady-state operation.

The maximum turn-on  $V_{GS}$  in Fig. 5 is equal to  $V_{OUT2}$ , since the FET switches on when the switch node pulls to ground. This places a limit on the maximum output voltage that  $V_{OUT2}$  can be, as many p-channel FETs have maximum  $V_{GS}$  ratings of only 8 V or 12 V. A maximum reverse  $V_{GS}$  equal to the input voltage ( $V_{IN}$ ) is applied when the switch node pulls to the input voltage and the output voltage is zero, which occurs at startup.

Fig. 6 shows a synchronous version of the circuit shown in Fig. 1c, using an n-channel FET for the auxiliary output. The gate-drive voltage for Q3 is derived from the gate-drive voltage of bottom FET Q2, allowing both FETs to switch

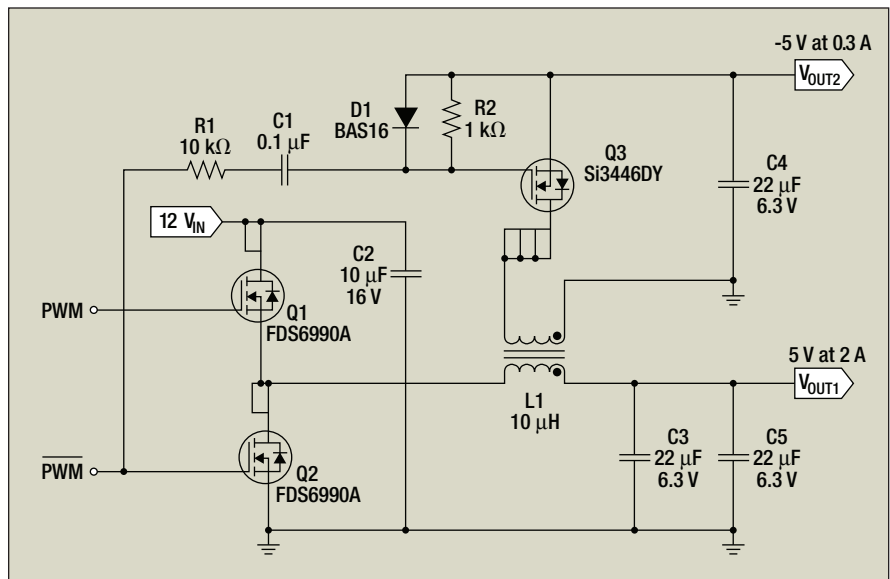


Fig. 6. A coupled inductor can produce a negative output voltage using a synchronous n-channel FET for rectification.

in phase with each other. Capacitor C1 ac-couples this switching signal, but blocks its dc average level. Diode D1 conducts only during the negative swing of the Q2 drive voltage, clamping Q3's gate voltage to 0.7 V below the source and turning it off.

# TW Paktron

multilayer polymer capacitors

[www.paktron.com](http://www.paktron.com)

## Mission Critical Applications

- MADE IN USA
- LONG-LIFE
- HIGH RELIABILITY

### MULTILAYER POLYMER (MLP) CAPACITORS

- Ultra low ESR and ESL
- High Ripple Current Handling
- Stable Under AC & DC Voltage
- Military/Telecom/Datacom 99.999% (5x9) Up Time
- Low Profile For Surface Mount
- Robust Mechanical and Electrical Design
- 50 to 500 Volts

### APPLICATIONS

- 48 Volt Telecom/Datacom
- HEV - Hybrid Electric Vehicle Boost Converters
- High Voltage Bus from 48 to 440+ Volts
- PFC Front Ends & SMPS Off-Line
- RFI/EMI Suppression

### AVAILABLE THROUGH THESE DISTRIBUTORS:

- |                          |                  |
|--------------------------|------------------|
| Atlantic Components      | (1-800-433-6600) |
| Cornell Dubilier/Mallory | (1-508-996-8561) |
| Future                   | (1-800-388-8731) |
| Gopher                   | (1-800-592-9519) |

1205 McConville Road ■ Lynchburg, Virginia 24502  
tel. 434.239.6941 ■ fax. 434.239.4730

[www.paktron.com](http://www.paktron.com)

During the positive swing of the Q2 drive voltage,  $V_{GS}$  for Q3 is equal to the Q2 gate-drive voltage, less a diode drop, turning it on. The use of 2.5- $V_{GS}$  threshold parts may be necessary if the gate-drive voltage is 4.5 V to 5 V. Without D1, the positive  $V_{GS}$  would vary with duty cycle, creating a situation where FET Q3 may not have enough drive voltage to turn on properly.

## Charge Pumps

The circuit in Fig. 7 is a boost converter with a charge pump that generates a negative auxiliary output voltage. The charge-pump circuit is composed of C2, C4, D3 and D4. When the FET turns off in a boost converter, the stored energy in the inductor is transferred to the output capacitor and load through diodes D1 and D2. At the same time, D4 conducts and C2 is charged to the output voltage plus a diode drop.

When the FET turns on again, the voltage on C2 pulls the charge-pump output negative through D3. The two diodes in the boost converter (D1 and D2) are necessary to cancel the forward-voltage drops of the two diodes in the charge pump (D3 and D4). Excellent voltage regulation is achieved for light loads on the (negative) charge-pump output.

The circuit in Fig. 8 is a charge pump that boosts the  $V_{OUT2}$  output voltage to the input voltage plus the  $V_{OUT1}$  output voltage. When the internal synchronous FET of the TPS62007 controller switches to ground, it charges C3 to the  $V_{OUT1}$  output voltage, less one diode drop. Then the internal control FET turns on, pulling U1 pin 9 to  $V_{IN}$ . This action forces the charge stored in C3 into output-capacitor C5.

As with most charge pumps, there are two diode drop reductions in the output voltage in Fig. 8. This circuit is useful in applications where the input voltage is well regulated or where the auxiliary output can feed the input to a linear regulator for a lower output voltage.

Fig. 9 is a variation of Fig. 8, but provides a negative output voltage at  $V_{OUT2}$ . The output voltage of the charge pump is equal to the inverted input voltage, less two diode drops.

The circuit in Fig. 10 is a multiple-output flyback using a stacked-winding transformer. Regulation is achieved by feedback from output  $V_{OUT2}$ . The addition of diode D1 and

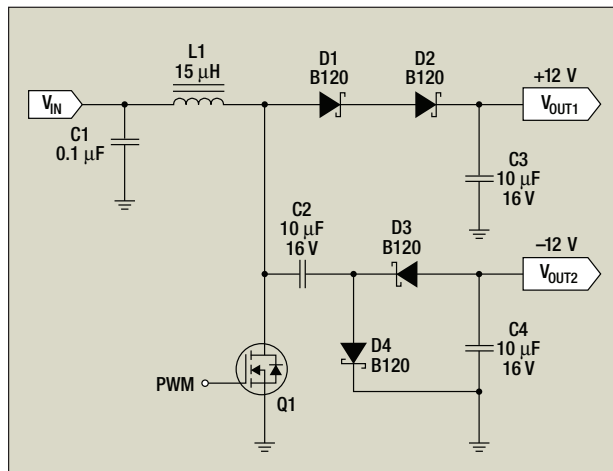


Fig. 7. When a boost converter is used to generate the main output ( $V_{OUT1}$ ), a charge pump can be added to generate a complementary, negative output voltage ( $V_{OUT2}$ ).

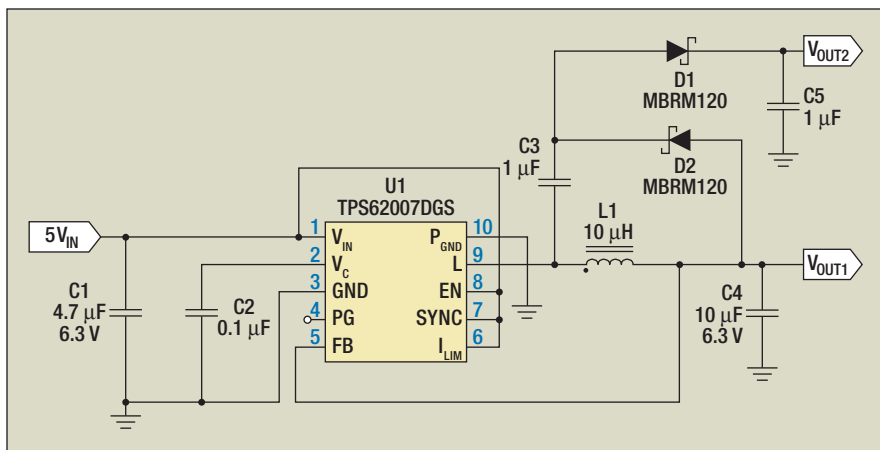


Fig. 8. A charge-pump circuit can produce an auxiliary output voltage ( $V_{OUT2}$ ) equal to the main output voltage ( $V_{OUT1}$ ), plus the input voltage minus two diode drops.

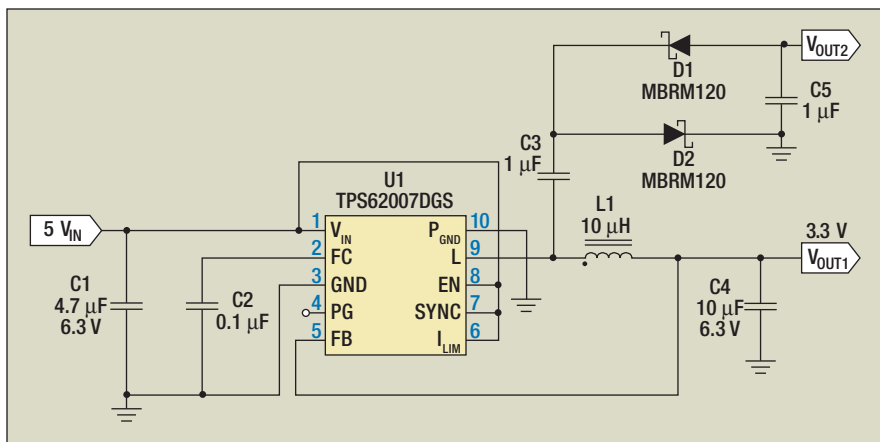


Fig. 9. An inverting charge pump provides a negative output voltage nearly equal to the positive input voltage. (The absolute values of  $V_{IN}$  and  $V_{OUT2}$  differ by two diode drops.)

C9 creates a negative-output  $V_{OUT4}$  that is equal in magnitude to  $V_{OUT2}$ .

Energy is transferred to all outputs only during the off time of FET Q1. During this interval, a negative voltage



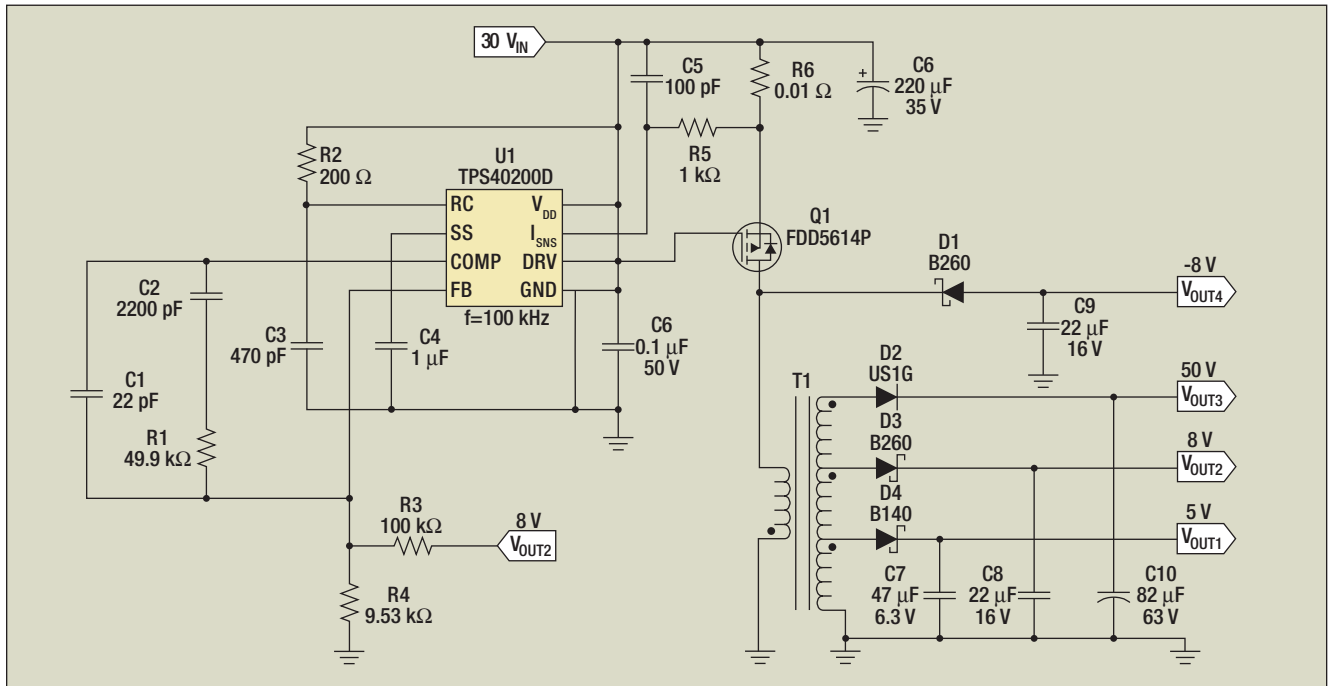


Fig. 10. A buck-boost converter joined with a flyback generates a series of auxiliary voltages ( $V_{OUT2}$ ,  $V_{OUT3}$  and  $V_{OUT4}$ ).

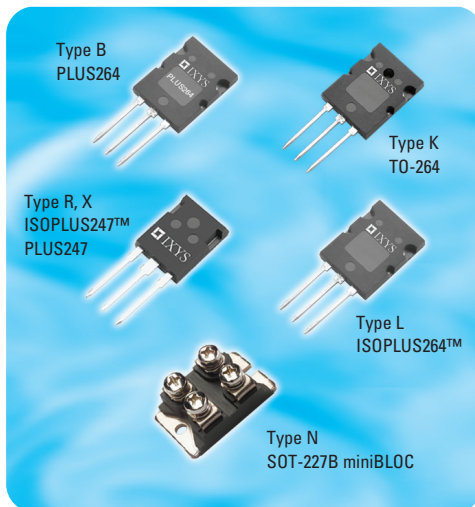
equal to  $V_{OUT2}$  is imposed across the primary winding, due to a 1:1 turns ratio between the primary winding and the  $V_{OUT2}$  stacked winding. With a negative  $V_{OUT2}$  clamped

across the primary winding, diode D1 charges capacitor C9, resulting in a voltage on output  $V_{OUT4}$  that is closely matched to  $V_{OUT2}$ .

PETech

## Improve Ruggedness and Dependability at Lower Cost... SIZE does matter!

### Higher Current (44A to 140A) 300V to 800V PolarHT™/HV™ Power MOSFETs



[www.ixys.com](http://www.ixys.com)

#### Features

- Up to 30% Lower  $R_{DS(on)}$  and  $Q_G$
- Lower thermal impedance and increased power handling
- Excellent ruggedness and dV/dt capability
- Incorporates fast intrinsic body diodes with very low  $Q_{rr}$  and  $I_{rr}$

#### Benefits

- Increased current handling capability
- Maximized package real estate
- ISOPLUS™ friendly
- Reduced component count
- Reduced circuit complexity
- Cost effective

#### PolarHT™/HV™ Product Family Part Numbers

Example Part Number: IX F 80 N 50 P

IXYS Part Number	T - Standard F - HiPerFET™	Package Type (1)	Current [A]	N-Channel	30 - 300V 50 - 500V 60 - 600V 80 - 800V	PolarHT™/HV™ Technology
IX	F	X, K, N, R(2)	140	N	30	P
IX	F	X, K, N, R(2)	80	N	50	P
IX	F	B, L, N	100	N	50	P
IX	F	X, K, N, R(2)	64	N	60	P
IX	F	B, L, N	82	N	60	P
IX	F	X, K, N, R(2)	44	N	80	P
IX	F	B, L, N	60	N	80	P

(1) Consult listed web links for specific die package combinations offered and parametric data.

(2) For information regarding IXYS ISOPLUS™ packages, visit <http://www.ixys.com/IXAN0022.pdf>

Complete list of Standard PolarHV™ MOSFETs can be found at <http://www.ixys.com/Appasp/pdmfet03.asp>

Complete list of PolarHV HiPerFET™ Power MOSFETs can be found at <http://www.ixys.com/Appasp/pdhfet02.asp>

ISOPLUS is a trademark of IXYS Corporation

Efficiency Through Technology

IXYS